

Yasunori Tokuda

List of Publications by Year in descending order

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97
papers

1,146
citations

430874

18
h-index

454955

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g-index

97
all docs

97
docs citations

97
times ranked

805
citing authors

#	ARTICLE	IF	CITATIONS
1	Remarkable breakdown voltage enhancement in AlGa _N channel high electron mobility transistors. Applied Physics Letters, 2008, 92, .	3.3	132
2	AlGa _N Channel HEMT With Extremely High Breakdown Voltage. IEEE Transactions on Electron Devices, 2013, 60, 1046-1053.	3.0	108
3	First Operation of AlGa _N Channel High Electron Mobility Transistors. Applied Physics Express, 2008, 1, 011101.	2.4	71
4	Fabrication of Terahertz Planar Metamaterials Using a Super-Fine Ink-Jet Printer. Applied Physics Express, 2010, 3, 016701.	2.4	64
5	Spectroscopic Characterization of Low-Temperature Grown GaAs Epitaxial Films. Japanese Journal of Applied Physics, 1994, 33, 4807-4811.	1.5	43
6	Distinct observation of interwell coupling effect on optical transitions in double quantum wells in an electric field. Applied Physics Letters, 1989, 54, 1232-1234.	3.3	34
7	Widely separate wavelength switching of single quantum well laser diode by injection current control. Applied Physics Letters, 1986, 49, 1629-1631.	3.3	29
8	Degradation Mode Analysis on Highly Reliable Guardring-Free Planar InAlAs Avalanche Photodiodes. Journal of Lightwave Technology, 2007, 25, 3686-3693.	4.6	29
9	Ion implantation doping for AlGa _N /Ga _N HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2364-2367.	0.8	27
10	Crossover from capacitive to inductive electromagnetic responses in near self-complementary metallic checkerboard patterns. Optics Express, 2014, 22, 24787.	3.4	27
11	Self-electro-optic effect based on anticrossing of excitonic transitions in a coupled quantum well structure. Applied Physics Letters, 1990, 56, 166-167.	3.3	26
12	Optical transmission anomalies in a double-layered metallic slit array. Optics Express, 2010, 18, 17876.	3.4	25
13	Parasitic Resistance Reduction in Deep Submicron Dual-Gate Transistors with Partially Elevated Source/Drain Extension Regions Fabricated by Complementary Metal-Oxide-Semiconductor Technologies. Japanese Journal of Applied Physics, 2000, 39, 387-389.	1.5	21
14	Application of AlAs/GaAs superlattices to step-index and graded-index waveguide separate-confinement heterostructure laser diodes. Journal of Applied Physics, 1986, 60, 2729-2734.	2.5	20
15	Effects of a thin Al layer insertion between AlGa _N and Schottky gate on the AlGa _N -Ga _N high electron mobility transistor characteristics. Applied Physics Letters, 2006, 88, 043503.	3.3	20
16	Enhancement of Drain Current by an AlN Spacer Layer Insertion in AlGa _N /Ga _N High-Electron-Mobility Transistors with Si-Ion-Implanted Source/Drain Contacts. Japanese Journal of Applied Physics, 2011, 50, 064101.	1.5	20
17	Enhancement of Drain Current by an AlN Spacer Layer Insertion in AlGa _N /Ga _N High-Electron-Mobility Transistors with Si-Ion-Implanted Source/Drain Contacts. Japanese Journal of Applied Physics, 2011, 50, 064101.	1.5	20
18	Observation of excitonic effects on electroabsorption in coupled quantum wells. Physical Review B, 1990, 41, 10280-10282.	3.2	19

#	ARTICLE	IF	CITATIONS
19	Drivability Enhancement for AlGaIn/GaN High-Electron Mobility Transistors with AlN Spacer Layer Using Si Ion Implantation Doping. Applied Physics Express, 0, 2, 031003.	2.4	18
20	Design and Characteristics of Guardring-Free Planar AlInAs Avalanche Photodiodes. Journal of Lightwave Technology, 2009, 27, 1011-1017.	4.6	18
21	Anomalous excitation intensity dependence of photoluminescence properties of an asymmetric coupled quantum well structure. Journal of Applied Physics, 1989, 65, 2168-2170.	2.5	14
22	Characterization of Crystallinity in Low-Temperature-Grown GaAs Layers by Raman Scattering and Time-Resolved Photoreflectance Measurements. Japanese Journal of Applied Physics, 1996, 35, 5955-5963.	1.5	14
23	Emission spectra of single quantum well lasers with inhomogeneous current injection. Journal of Applied Physics, 1988, 64, 1022-1026.	2.5	13
24	Low thermal budget surface cleaning after dry etching for selective silicon epitaxial growth. Journal of Crystal Growth, 2001, 226, 443-450.	1.5	12
25	Optical Phased Array Functions in Double-Layered Metallic Plate Systems with Artificially Modulated Slit Arrays. Applied Physics Express, 2012, 5, 042502.	2.4	12
26	Remarkable Breakdown Voltage Enhancement in AlGaIn Channel HEMTs. , 2007, , .		11
27	Lowest-order axial and ring mode lasing in confocal quasi-stadium laser diodes. Applied Optics, 2012, 51, 2515.	1.8	11
28	On the Origin of Oval Defect with Nucleus on Epilayers Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1986, 25, 908-909.	1.5	10
29	Dual wavelength emission from a twin stripe single quantum well laser. Applied Physics Letters, 1987, 51, 1664-1666.	3.3	10
30	Lasing wavelength of an asymmetric double quantum well laser diode. Applied Physics Letters, 1987, 51, 209-211.	3.3	10
31	Multistable behavior of connected bistable devices. Journal of Applied Physics, 1994, 75, 3749-3755.	2.5	10
32	Advantage of Shallow Trench Isolation over Local Oxidation of Silicon on Alignment Tolerance. Japanese Journal of Applied Physics, 1999, 38, L234-L235.	1.5	10
33	Self-deformed and hysteretic photocurrent spectra of quantum wells with a load resistor. Applied Physics Letters, 1989, 54, 2324-2326.	3.3	9
34	Dual wavelength multiple quantum well infrared photodetector using an optically bistable abrupt absorption edge. Applied Physics Letters, 1990, 56, 227-229.	3.3	9
35	Triple excitonic mixing associated with recoupling of a Stark-localized state in coupled quantum wells confined by superlattices. Physical Review B, 1991, 43, 7170-7173.	3.2	9
36	Analysis of Single-Photon-Detection Characteristics of GaInAs/InP Avalanche Photodiodes. IEEE Journal of Quantum Electronics, 2010, 46, 1444-1449.	1.9	9

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37	Spectroscopic Functions of Multi-Stacked Metallic Plates with Modulated Slit Arrays. Applied Physics Express, 2013, 6, 062602.	2.4	9
38	Optical bistable responses based on self-electro-optic effect in a nonbiased asymmetric coupled quantum well photodiode. Applied Physics Letters, 1993, 62, 2492-2494.	3.3	8
39	Significant effect of lateral resistivity on optical nonlinear responses of a quantum well photodiode. Applied Physics Letters, 1993, 63, 3259-3261.	3.3	8
40	Significant Effects of As Ion Implantation on Si-selective Epitaxy by Ultrahigh Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1999, 38, 5046-5047.	1.5	8
41	Self-pulsation and optical injection locking for multielectrode distributed feedback lasers using phase-shift-induced modes. Applied Physics Letters, 2004, 85, 4840-4841.	3.3	8
42	Look out! Nature Photonics, 2009, 3, 7-8.	31.4	8
43	Investigation of fade-out mechanism of resonance modes in optical transmission using stacked metallic sub-wavelength slit arrays. Journal of Applied Physics, 2014, 115, 243104.	2.5	8
44	Complex multistable responses of serially connected optical bistable devices. Applied Physics Letters, 1991, 59, 1016-1018.	3.3	7
45	Si Deposition into Fine Contact Holes by Ultrahigh-Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1999, 38, 4045-4046.	1.5	7
46	Epitaxial Si _{1-x} Ge _x grown into fine contact hole by ultrahigh-vacuum chemical vapor deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 68, 171-174.	3.5	7
47	Remarkable transmission characteristics of optical waves through modulated double-layered metallic slit arrays. AIP Advances, 2012, 2, 042112.	1.3	7
48	Tuning the effective refractive index of a thin air gap region sandwiched by metallic metamaterials by lateral displacements. Journal of Applied Physics, 2013, 113, .	2.5	7
49	Crossing behaviors of optical resonance modes in metallic metamaterials. Applied Physics Express, 2016, 9, 032201.	2.4	7
50	Novel spectral response of a coupled quantum well photodiode. Applied Physics Letters, 1990, 56, 2166-2168.	3.3	6
51	Lasing of TM modes in a two-dimensional GaAs microlaser. Optics Express, 2014, 22, 11912.	3.4	6
52	Waveguide resonance mode response of stacked structures of metallic sub-wavelength slit arrays. Journal of Applied Physics, 2018, 123, .	2.5	6
53	Carrier-Temperature and Wavelength-Switching in GaAs Single-Quantum-Well Baser Diode. Japanese Journal of Applied Physics, 1986, 25, L931-L933.	1.5	4
54	Incident wavelength dependence of photocurrent bistability by external bias voltage control in a quantum well photodiode. Applied Physics Letters, 1989, 55, 711-712.	3.3	4

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55	Step-Promoted Surface Reconstruction on Ga-Deposited (100) GaAs During Molecular Beam Epitaxy with Alternating Supply of Ga and As. Japanese Journal of Applied Physics, 1991, 30, 3491-3495.	1.5	4
56	Optically reversible switching between binary states using multistable loops. Applied Physics Letters, 1993, 63, 2609-2611.	3.3	4
57	Anomalous Gate Length Dependence of Threshold Voltage of Trench-Isolated Metal Oxide Semiconductor Field Effect Transistors. Japanese Journal of Applied Physics, 1998, 37, L852-L854.	1.5	4
58	Selective Epitaxial Growth by Ultrahigh-Vacuum Chemical Vapor Deposition with Alternating Gas Supply of Si ₂ H ₆ and Cl ₂ . Japanese Journal of Applied Physics, 2000, 39, 6139-6142.	1.5	4
59	Very High Frequency Self-Pulsation and Stable Optical Injection Locking for Well-Defined Multi-Electrode Distributed Feedback Lasers. Japanese Journal of Applied Physics, 2004, 43, 1965-1968.	1.5	4
60	Guardring-Free Planar AlInAs Avalanche Photodiodes for 2.5-Gb/s Receivers With High Sensitivity. IEEE Photonics Technology Letters, 2007, 19, 765-767.	2.5	4
61	Selective excitation of lowest-order transverse ring modes in a quasi-stadium laser diode. Optics Letters, 2013, 38, 4158.	3.3	4
62	Light propagation in a Penrose unilluminable room. Optics Express, 2015, 23, 17431.	3.4	4
63	Multiple intersection properties of optical resonance modes in metallic metamaterials. AIP Advances, 2017, 7, .	1.3	4
64	Optical nonlinear responses of a quantum well photodiode with a non-ohmic contact. Applied Physics Letters, 1992, 60, 1664-1666.	3.3	3
65	Narrow-Channel Metal Oxide Semiconductor Field Effect Transistor (MOSFET) Isolated by an Ultra-Fine Trench. Japanese Journal of Applied Physics, 1997, 36, L547-L549.	1.5	3
66	Thermal robustness in synthetic antiferromagnetic free layer for magnetic random access memory applications. Journal of Applied Physics, 2006, 99, 08C911.	2.5	3
67	Efficient incorporation of a nonnatural amino acid into a protein in an insect cell-free translation system. Nucleic Acids Symposium Series, 2006, 50, 277-278.	0.3	3
68	Laser diode beam shaping by optical interference. Optical Review, 2011, 18, 287-292.	2.0	3
69	Insertion effects of natural dielectric between artificial dielectrics formed by metallic sub-wavelength slit arrays. AIP Advances, 2018, 8, .	1.3	3
70	Photoluminescence of a Novel Heteron-i-p-i Structure Incorporating Triple Quantum Wells. Japanese Journal of Applied Physics, 1989, 28, L747-L749.	1.5	2
71	All-optical bistability of a p-i-p-i-n device with GaAs/AlAs coupled-quantum-well absorption layers and an AlAs resistive layer. Optics Letters, 1993, 18, 885.	3.3	2
72	Electrical Characteristics of Ultra-Fine Trench Isolation Fabricated by a New Two-Step Filling Process. Japanese Journal of Applied Physics, 1996, 35, L1625-L1627.	1.5	2

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73	Protection of Field Oxide in Trench Isolation against Contact Hole Etching to Improve Alignment Tolerance. Japanese Journal of Applied Physics, 1998, 37, L833-L835.	1.5	2
74	Remarkable Effects of Introduction of SiON Materials into Shallow Trench Isolation Fabrication Process on Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2001, 40, 462-466.	1.5	2
75	Planar Avalanche Photodiode for Long-Haul Single-Photon Optic Fiber Communications. Applied Physics Express, 2008, 1, 012001.	2.4	2
76	Marked effects of lateral displacement on the optical transmission properties of stacked artificial dielectric systems composed of metallic sub-wavelength slit arrays. Japanese Journal of Applied Physics, 2019, 58, 122004.	1.5	2
77	Ray Dynamical Simulation of Penrose Unilluminable Room Cavity. , 2013, , .		2
78	External bias voltage and incident light intensity dependent effects of quantum-confined excitonic transitions on bulk background photocurrent spectra. Journal of Applied Physics, 1994, 75, 1620-1622.	2.5	1
79	Improvement of alignment tolerance against contact hole etching by growing of underlying silicon-selective epitaxial layer. Microelectronic Engineering, 2001, 56, 281-287.	2.4	1
80	A Dual-Gate Complementary Metal-Oxide-Semiconductor Technology with Novel Self-Aligned Pocket Implantation which Takes Advantage of Elevated Source/Drain Configurations. Japanese Journal of Applied Physics, 2001, 40, 2611-2615.	1.5	1
81	All-Optical Clock Recovery and Wavelength Conversion by Combination of Self-Pulsation Laser and Semiconductor-Optical-Amplifier-Based Mach-Zehnder Interferometer. Japanese Journal of Applied Physics, 2006, 45, 3457-3461.	1.5	1
82	X-ray Photoelectron Spectroscopy Study of the Origin of the Improved Device Performance by a Thin Al Layer Insertion between AlGa _N and Schottky Gate on the AlGa _N /Ga _N High-Electron-Mobility Transistor. Japanese Journal of Applied Physics, 2007, 46, L584-L586.	1.5	1
83	Lasing Mechanism Analysis of Self-Pulsating Distributed Feedback Laser Diodes and Successful Demonstration of All-Optical Signal Recovery at 40 Gbps. Japanese Journal of Applied Physics, 2008, 47, 3493-3498.	1.5	1
84	Fast beam switching operation of two-dimensional microcavity laser diode. , 2016, , .		1
85	Room-Temperature Self-Electrooptic Effects of GaAs/AlAs Asymmetric Coupled Quantum Wells. Japanese Journal of Applied Physics, 1991, 30, L963-L965.	1.5	0
86	Experimental study on isolation edge effects in the short channel characteristics of metal oxide semiconductor field effect transistors (MOSFETs). Microelectronic Engineering, 1999, 45, 369-375.	2.4	0
87	Surface Defect Formation in Epitaxial Si Grown on Boron-Doped Substrates by Ultrahigh Vacuum Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2001, 40, L1051-L1053.	1.5	0
88	Resonator modes in a two-dimensional quasi-stadium laser diode with concave end mirrors. , 2010, , .		0
89	Resonator Modes of Quasi-Stadium Laser Diodes with Unstable Optical Cavities. The Review of Laser Engineering, 2011, 39, 537-542.	0.0	0
90	Quality factor of laser diode beam tailored by Lloyd's mirror interference. , 2011, , .		0

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91	Selective excitation of lowest-order axial and ring modes in confocal quasi-stadium laser diodes. , 2011, , .		0
92	Quality factor of circular laser diode beam tailored by optical interference. Optical Review, 2012, 19, 328-331.	2.0	0
93	Analysis of resonator modes in two-dimensional laser cavities containing a left-handed material. Optical Review, 2013, 20, 293-295.	2.0	0
94	Compact Two-Dimensional Multipass GaAs Optical Cavity with a Long Path Length. , 2014, , .		0
95	Transverse magnetic emissions of GaAs unstrained quantum-well microcavity lasers. , 2015, , .		0
96	Quasi-dielectric characteristics of stacked metallic metamaterials. Japanese Journal of Applied Physics, 2017, 56, 030306.	1.5	0
97	Nondestructive mixing characteristics of optical resonance modes investigated using artificial dielectric systems. AIP Advances, 2020, 10, .	1.3	0